

Performance

- Frequency: 9.0~10.2GHz
- Linear Gain: 27dB
- Saturation Output Power: 41dBm
- Power Added Efficiency: 43%
- Bias Condition: 8V, -0.6V
- Size: 3.2*4.0mm*0.08mm
- Process: 0.35um PHEMT Technology

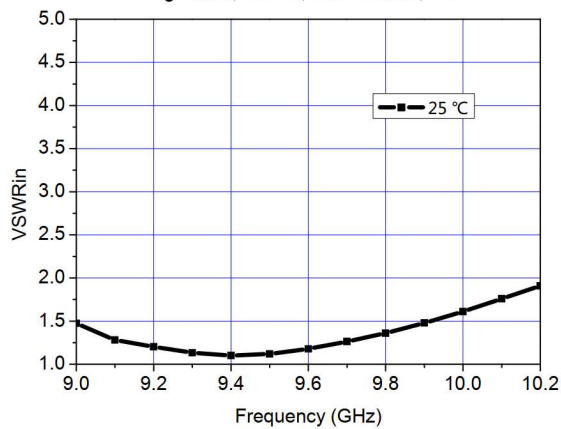
Electrical Specifications (Vd=8V, Vg= -0.6V, Freq=9.0~10.2GHz)

Symbol	Parameter	Min	Typical	Max	Unit
G	Linear Gain	-	27	-	dB
G _P	Power Gain	-	24	-	dB
P _{sat}	Saturated Power	40.7	41	-	dBm
PAE	Power Added Efficiency	40	43	-	%
R _{θj}	Thermal Resistance (Vd=8V, Pdiss=18W)		2.7		°C/W

Test Curves

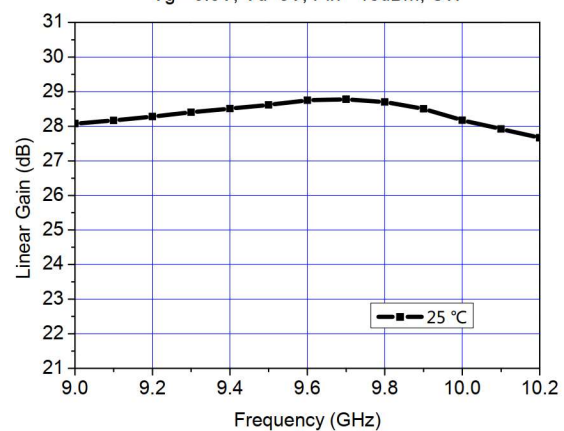
Input VSWR vs. Freq

Vg=-0.6V, Vd=8V, Pin=-15dBm, CW



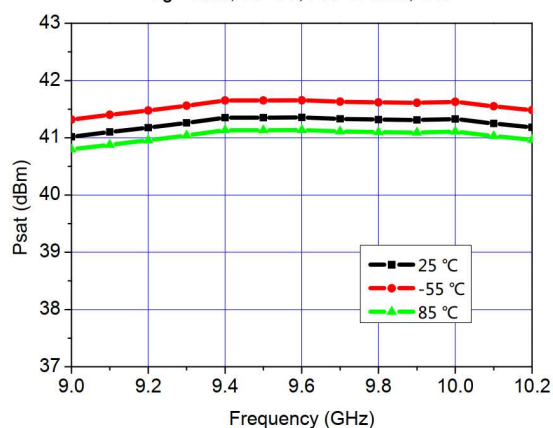
Linear Gain vs. Freq

Vg=-0.6V, Vd=8V, Pin=-15dBm, CW



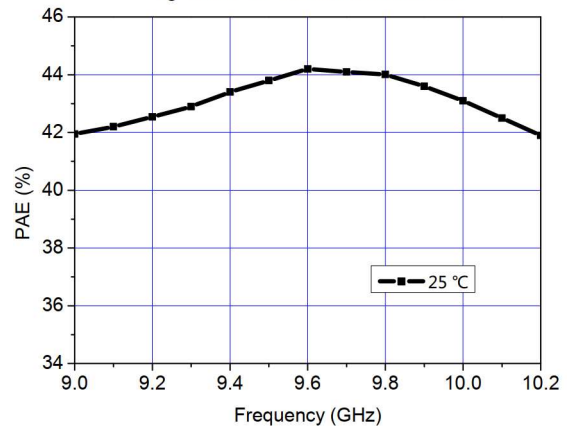
Saturation Output Power vs. Freq

Vg=-0.6V, Vd=8V, Pin=17dBm, CW



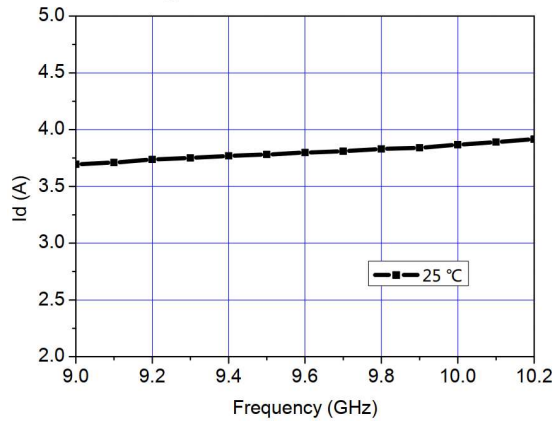
PAE vs. Freq

Vg=-0.6V, Vd=8V, Pin=17dBm, CW



Drain Current

V_g=-0.6V, V_d=8V, Pin=17dBm, CW



Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	9V	
I _d	Drain Current	6A	
V _g	Gate Voltage	-2V	
I _g	Gate Current	100mA	
P _d	DC Power Consumption	45W	
P _{in}	Input Power	28dBm	
T _{ch}	Channel Temperature	150°C	
T _m	Mounting Temperature	300°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~150°C	

Exceeding any one or combination of these limits may cause permanent damage.

